

**UNISONIC TECHNOLOGIES CO., LTD** 

## DTC144T

### NPN SILICON TRANSISTOR

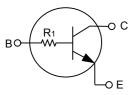
# NPN DIGITAL TRANSISTOR (BUILT- IN BIAS RESISTORS)

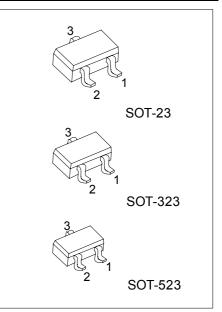
### FEATURES

\* Built-in bias resistors that implies easy ON/OFF applications.

\* The bias resistors are thin-film resistors with complete isolation to allow negative input.

#### EQUIVALENT CIRCUIT





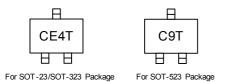
\*Pb-free plating product number:DTC144TL

#### ORDERING INFORMATION

Order Number		Deekege	Pin Assignment			Decking	
Normal	Lead Free Plating	Package	1	2	3	Packing	
DTC144T-AE3-R	DTC144TL-AE3-R	SOT-23	Е	В	С	Tape Reel	
DTC144T-AL3-R	DTC144TL-AL3-R	SOT-323	Е	В	С	Tape Reel	
DTC144T-AN3-R	DTC144TL-AN3-R	SOT-523	Е	В	С	Tape Reel	

DTC144TL-AE3-R	(1)Packing Type	(1) R: Tape Reel
	(2)Package Type	(2) AE3: SOT-23, AL3: SOT-323, AN3: SOT-523
	(3)Lead Plating	(3) L: Lead Free Plating, Blank: Pb/Sn

#### MARKING



#### ■ ABSOLUTE MAXIMUM RATINGS (Ta = 25 )

PARAMETER		SYMBOL	RATING	UNIT
Collector-Base Voltage		V <sub>CBO</sub>	50	V
Collector-Emitter Voltage		V <sub>CEO</sub>	50	V
Emitter-Base Voltage		V <sub>EBO</sub>	5	V
Collector Current		lc	100	mA
Collector Dower Discinction	SOT-523	Б	150	mW
Collector Power Dissipation	SOT-23/SOT-323	Pc	200	mW
Junction Temperature		TJ	150	
Storage Temperature		T <sub>STG</sub>	-55~+150	

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

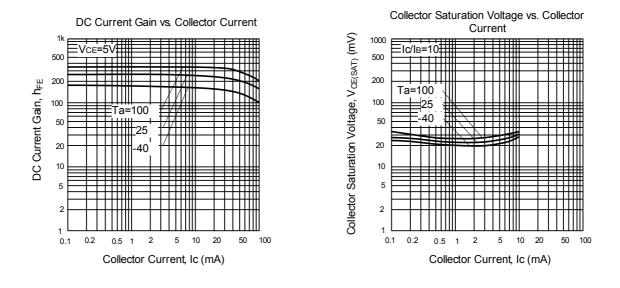
#### ■ ELECTRICAL CHARACTERISTICS (Ta= 25 , unless otherwise specified)

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$BV_{CBO}$	Ι <sub>C</sub> =50μΑ	50			V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	I <sub>C</sub> =1mA	50			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	I <sub>E</sub> =50μA	5			V
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =50V			0.5	μA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =4V			0.5	μA
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	I <sub>C</sub> =5mA, I <sub>B</sub> =0.5mA			0.3	V
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =1mA	100	250	600	
Input Resistance	R1		32.9	47	61.1	kΩ
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>E</sub> =-5mA, f=100MHz*		250		MHz

\* Transition frequency of the device



#### **TYPICAL CHARACTERISTICS**



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